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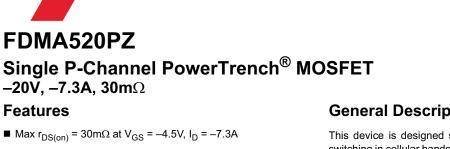


## **ON Semiconductor**®

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- Max  $r_{DS(on)}$  = 53m $\Omega$  at V<sub>GS</sub> = -2.5V, I<sub>D</sub> = -5.5A
- Low profile 0.8mm maximum in the new package MicroFET 2X2 mm
- HBM ESD protection level > 3kV typical (Note 3)
- Free from halogenated compounds and antimony oxides
- RoHS Compliant

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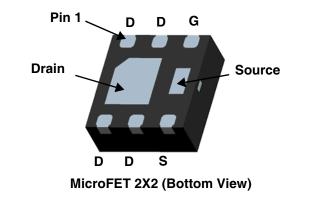


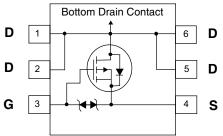
#### **General Description**

This device is designed specifically for battery charge or load switching in cellular handset and other ultraportable applications. It features a MOSFET with low on-state resistance.

June 2014

The MicroFET 2X2 package offers exceptional thermal performance for its physical size and is well suited to linear mode applications.





#### MOSFET Maximum Ratings T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units
V <sub>DS</sub>	Drain to Source Voltage		-20	V
V <sub>GS</sub>	Gate to Source Voltage		±12	V
1	Drain Current -Continuous	(Note 1a)	-7.3	_
D	-Pulsed		-24	— A
D	Power Dissipation	(Note 1a)	2.4	W
P <sub>D</sub>	Power Dissipation	(Note 1b)	0.9	vv
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C

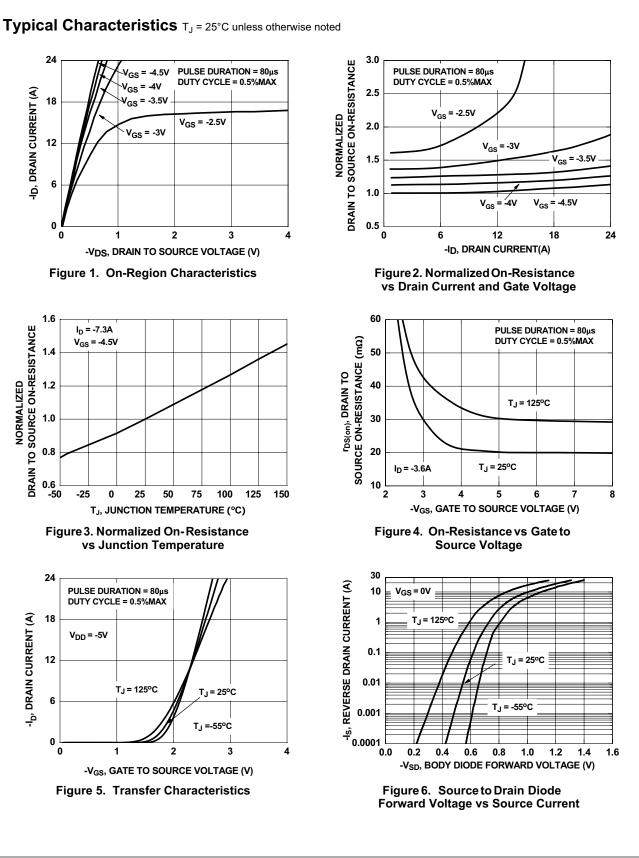
#### **Thermal Characteristics**

R <sub>0JA</sub>	Thermal Resistance, Junction to Ambient	(Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	145	0/11

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
520	FDMA520PZ	MicroFET 2X2	7"	8mm	3000 units

Off Chara BV <sub>DSS</sub> ΔBV <sub>DSS</sub> ΔT <sub>J</sub> I <sub>DSS</sub>	cteristics Drain to Source Breakdown Voltage		Min	Тур	Max	Units
BV <sub>DSS</sub> ΔBV <sub>DSS</sub> ΔT <sub>J</sub>						
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>		I <sub>D</sub> = –250μA, V <sub>GS</sub> = 0V	-20			V
	Breakdown Voltage Temperature Coefficient	$I_D = -250 \mu A$ , referenced to 25°C		-8.4		mV/°C
	Zero Gate Voltage Drain Current	$V_{DS} = -16V, V_{GS} = 0V$			-1	μA
GSS	Gate to Source Leakage Current	$V_{GS} = \pm 12V, V_{DS} = 0V$			±10	μA
On Chara	cteristics					
	Gate to Source Threshold Voltage	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = -250μA	-0.6	-1.1	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_{.1}}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = -250 \mu A$ , referenced to 25°C	-0.0	3.5	-1.5	mV/°C
Δīj		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -7.3A		26	30	-
DS(on)	Static Drain to Source On Resistance	$V_{GS} = -2.5V, I_D = -5.5A$		42	53	mΩ
D3(01)		$V_{GS} = -4.5V, I_D = -7.3A, T_J = 125^{\circ}C$		36	55	
9FS	Forward Transconductance	$V_{\rm DS} = -5V, I_{\rm D} = -7.3A$		22		S
	Characteristics			1		
	Input Capacitance			1235	1645	pF
C <sub>oss</sub>	Output Capacitance	$-V_{DS} = -10V, V_{GS} = 0V,$		255	340	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f = 1MHz		225	340	pF
Switching	Characteristics	V <sub>DD</sub> = -10V, I <sub>D</sub> = -7.3A				
t <sub>d(on)</sub>	J Characteristics         Turn-On Delay Time         Rise Time			10 29	20 47	ns ns
td(on) tr td(off)	Turn-On Delay Time Rise Time Turn-Off Delay Time	$V_{DD} = -10V, I_D = -7.3A$ $V_{GS} = -4.5V, R_{GEN} = 6\Omega$		29 83	47 133	ns ns
td(on) tr td(off) tf	Turn-On Delay Time Rise Time Turn-Off Delay Time Fall Time			29 83 74	47 133 119	ns ns ns
d(on) r d(off) f Q <sub>g</sub>	Turn-On Delay Time         Rise Time         Turn-Off Delay Time         Fall Time         Total Gate Charge	$V_{GS} = -4.5V, R_{GEN} = 6\Omega$		29 83 74 14	47 133	ns ns ns nC
td(on) tr td(off) tf Qg Qgs	Turn-On Delay TimeRise TimeTurn-Off Delay TimeFall TimeTotal Gate ChargeGate to Source Gate Charge			29 83 74 14 2.9	47 133 119	ns ns nC nC
t <sub>d(on)</sub> tr t <u>d(off)</u> tf Qg Qgs Qgd	Turn-On Delay TimeRise TimeTurn-Off Delay TimeFall TimeTotal Gate ChargeGate to Source Gate ChargeGate to Drain "Miller" Charge	$V_{GS} = -4.5V, R_{GEN} = 6Ω$ 		29 83 74 14	47 133 119	ns ns ns nC
ر ۲ ۲ ۲ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵ ۵	Turn-On Delay Time         Rise Time         Turn-Off Delay Time         Fall Time         Total Gate Charge         Gate to Source Gate Charge         Gate to Drain "Miller" Charge         Irce Diode Characteristics	$V_{GS} = -4.5V, R_{GEN} = 6Ω$ $V_{DD} = -5V, I_D = -7.3A$ $V_{GS} = -4.5V$		29 83 74 14 2.9	47 133 119 20	ns ns nC nC nC
ر مر م م م م م م م م م م م م م م م م م	Turn-On Delay Time         Rise Time         Turn-Off Delay Time         Fall Time         Total Gate Charge         Gate to Source Gate Charge         Gate to Drain "Miller" Charge         Irce Diode Characteristics         Maximum Continuous Drain-Source Diode	$V_{GS} = -4.5V, R_{GEN} = 6\Omega$ $V_{DD} = -5V, I_D = -7.3A$ $V_{GS} = -4.5V$ de Forward Current		29 83 74 14 2.9 4.4	47 133 119 20 -2	ns ns nC nC nC
t <sub>d(on)</sub> tr t <u>d(off)</u> tf Qg Qgs Qgd	Turn-On Delay Time         Rise Time         Turn-Off Delay Time         Fall Time         Total Gate Charge         Gate to Source Gate Charge         Gate to Drain "Miller" Charge         Irce Diode Characteristics	$V_{GS} = -4.5V, R_{GEN} = 6Ω$ $V_{DD} = -5V, I_D = -7.3A$ $V_{GS} = -4.5V$		29 83 74 14 2.9	47 133 119 20	ns ns nC nC nC

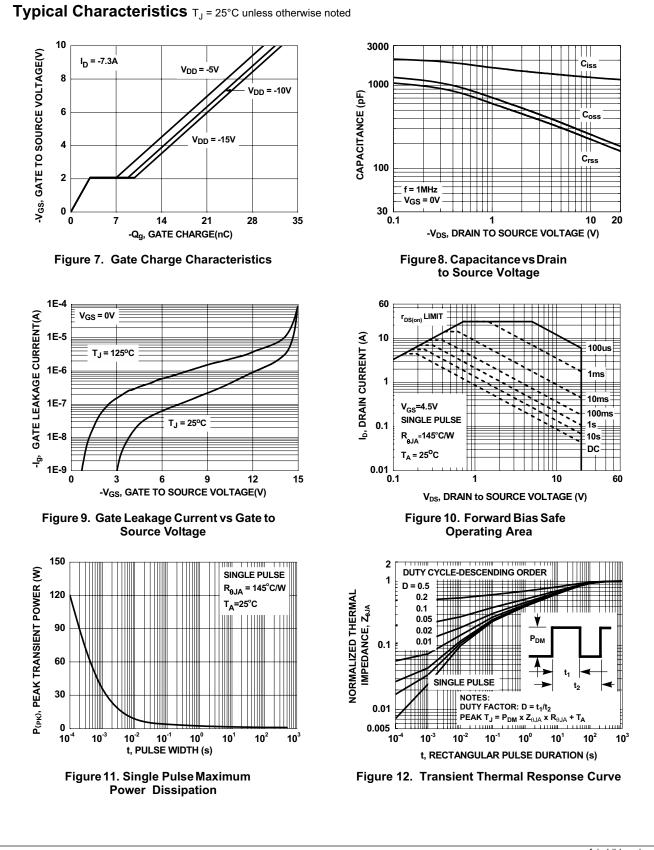


FDMA520PZ Rev.B3

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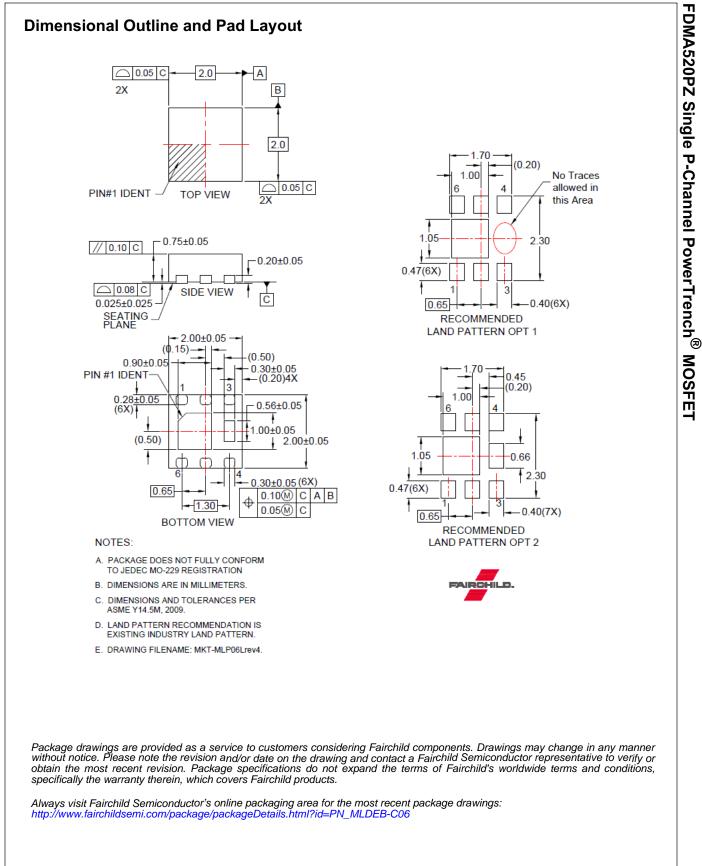


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Obsolete

Not In Production

Datasheet contains specifications on a product that is discontinued by Fairchild

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